



### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
30V	2.6m $\Omega$ @10V	90A
	3.9m $\Omega$ @4.5V	

### Feature

- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

### Application

- Power Switching Application

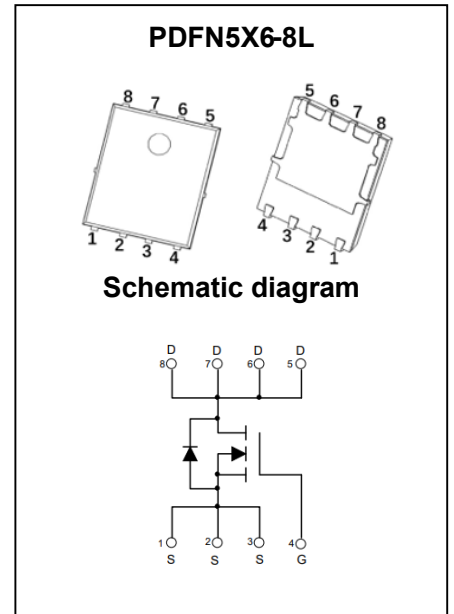
### MARKING:



M026N03L = Device Code  
XX = Date Code  
Solid Dot = Green Indicator

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	30	V
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1</sup>	$T_C = 25^\circ\text{C}$	$I_D$	90 A
	$T_C = 100^\circ\text{C}$	$I_D$	57 A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	360	A
Single Pulsed Avalanche Current <sup>3</sup>	$I_{AS}$	35	A
Single Pulsed Avalanche Energy <sup>3</sup>	$E_{AS}$	306	mJ
Power Dissipation <sup>5</sup>	$T_C = 25^\circ\text{C}$	$P_D$	47 W
Thermal Resistance from Junction to Ambient <sup>6</sup>	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	3	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$



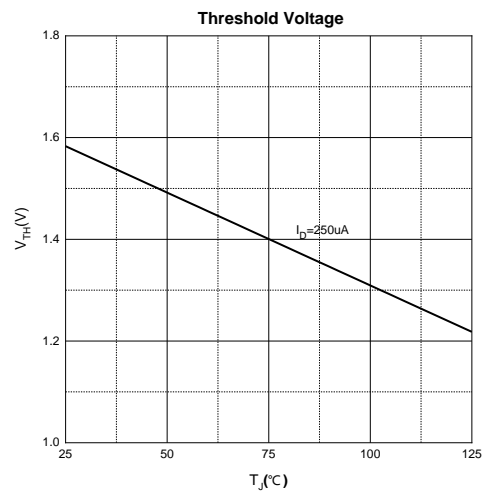
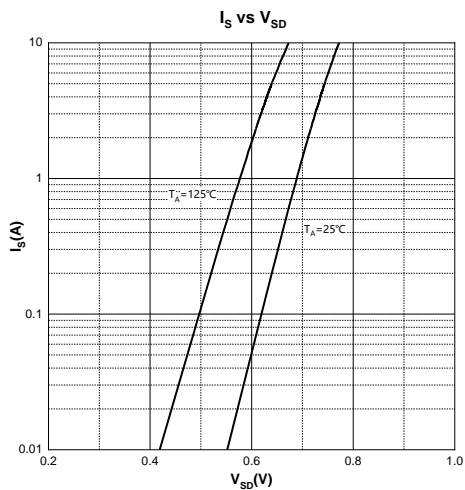
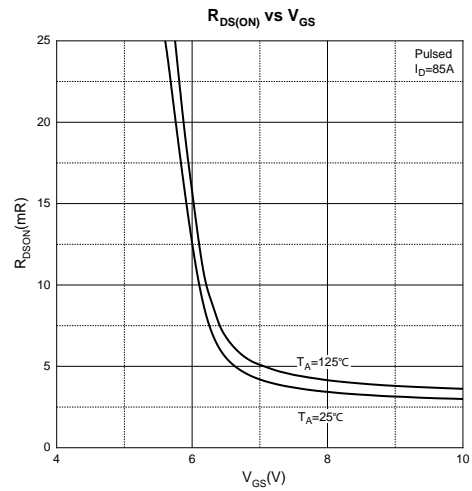
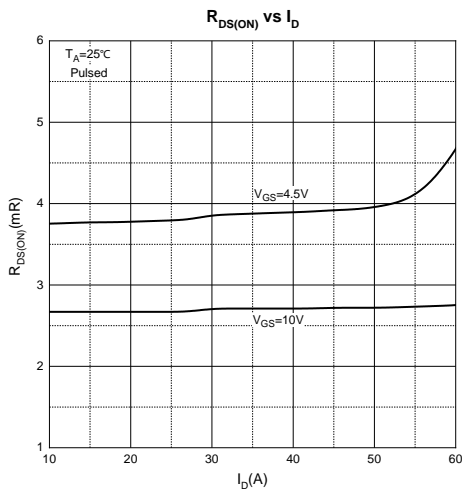
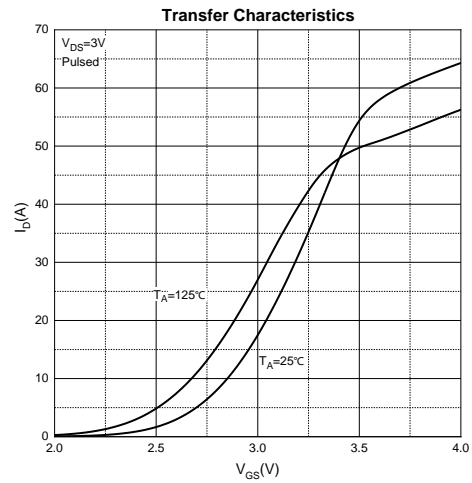
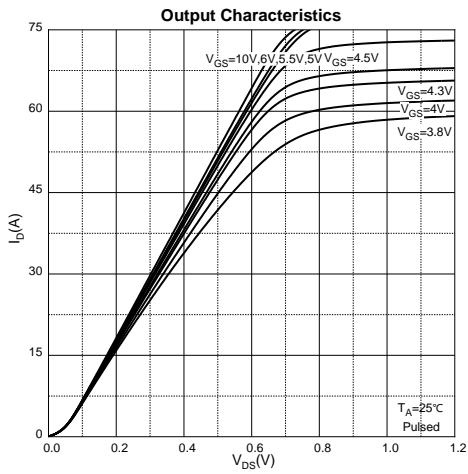
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

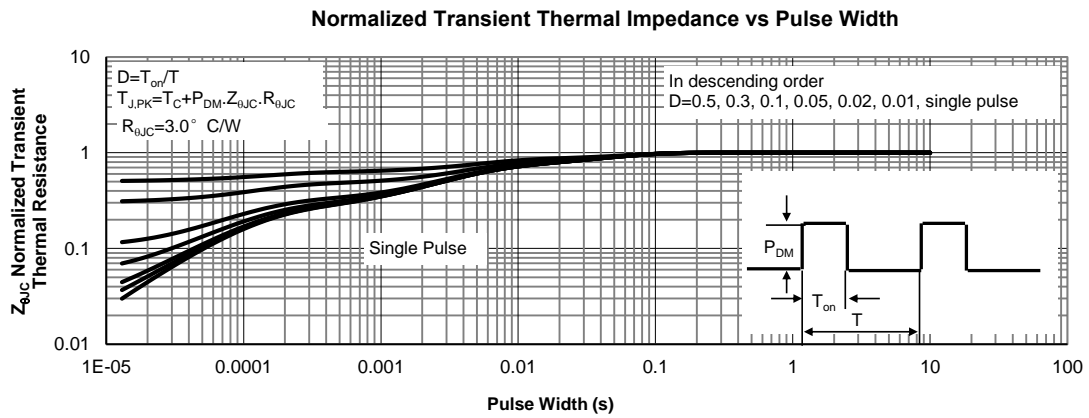
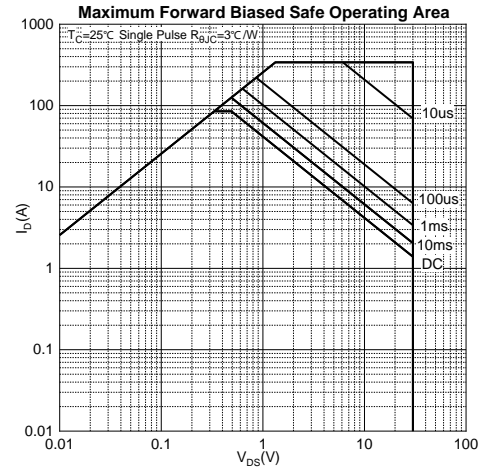
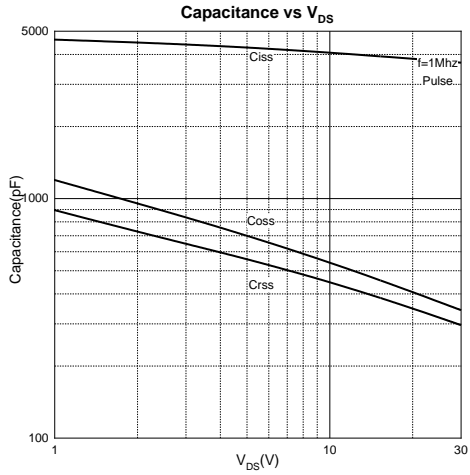
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>4</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.6	3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		2.6	3.2	m $\Omega$
		$V_{GS} = 4.5V, I_D = 15A$		3.9	5.5	
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$		3952		pF
Output Capacitance	$C_{oss}$			459		
Reverse Transfer Capacitance	$C_{rss}$			389		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.8		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 25V, V_{GS} = 10V, I_D = 20A$		78		nC
Gate-source Charge	$Q_{gs}$			11		
Gate-drain Charge	$Q_{gd}$			19		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 5V, V_{GS} = 10V, I_D = 20A,$ $R_G = 6\Omega$		10		ns
Turn-on Rise Time	$t_r$			8		
Turn-off Delay Time	$t_{d(off)}$			35		
Turn-off Fall Time	$t_f$			12		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 10A$			1.2	V

Notes :

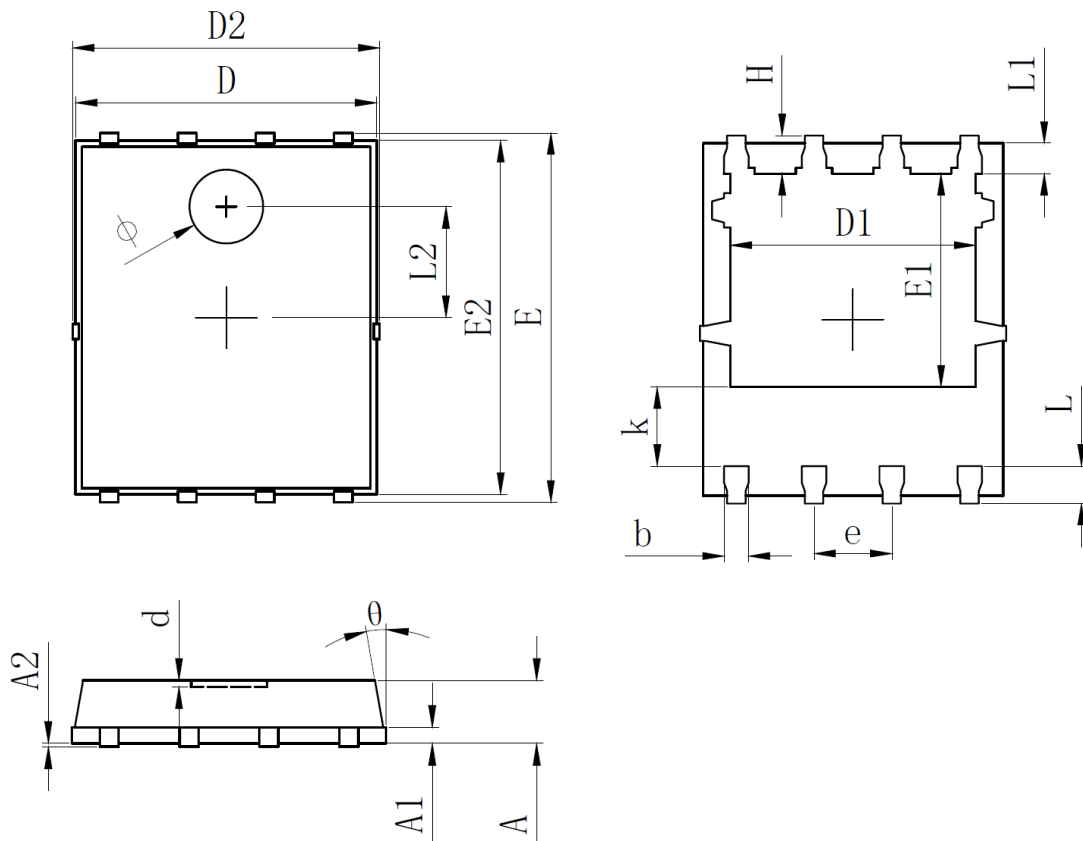
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.EAS condition:  $V_{DD} = 15V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$  Starting  $T_J = 25^\circ\text{C}$ .
- 4.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 5.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .And device mounted on a large heatsink
- 6.Device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

## Typical Characteristics





## PDFN5X6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.254REF		0.010REF	
A2	0.000	0.050	0.000	0.002
D	4.824	4.976	0.190	0.196
D1	3.910	4.110	0.154	0.162
D2	4.924	5.076	0.194	0.200
E	5.924	6.076	0.233	0.239
E1	3.375	3.575	0.133	0.141
E2	5.674	5.826	0.223	0.229
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.534	0.686	0.021	0.027
L1	0.424	0.576	0.017	0.023
k	1.190	1.390	0.047	0.055
H	0.549	0.701	0.022	0.028
θ	8°	12°	8°	12°
Φ	1.100	1.300	0.043	0.051
d	-	0.100	-	0.004